

Title (en)

NOVEL ORGANOCUPROUS PRECURSORS FOR CHEMICAL VAPOR DEPOSITION OF A COPPER FILM

Title (de)

NEUE ORGANOKUPFER-VORLÄUFER FÜR CVD VON KUPFERFILMEN

Title (fr)

NOUVEAUX PRECURSEURS ORGANO-CUIVREUX DESTINES AU DEPOT CHIMIQUE EN PHASE VAPEUR D'UN FILM DE CUIVRE

Publication

EP 1102872 A4 20080430 (EN)

Application

EP 99959960 A 19991207

Priority

- KR 9900743 W 19991207
- KR 19990013236 A 19990415

Abstract (en)

[origin: WO0063461A1] An organocuprous compound of formula (I) of the present invention can be conveniently used in a low-temperature CVD process for the mass production of a contaminant-free copper film having good thermal stability, wherein: R1, R2 and R3 are each independently a C1-8 alkoxy, aryl or aryloxy group, R4 and R5 are each independently hydrogen, fluorine, a C_nF_{2n+1} or C_nH_{2n+1} group, n being an integer in the range of 1 to 6, R6 is hydrogen, fluorine or C1-4 alkyl group, and m is 1 or 2, when m is 1, C=C represents C2C, and when m is 2, C=C represents C=C.

IPC 1-7

C23C 18/38

IPC 8 full level

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CPC (source: EP KR)

C07F 1/08 (2013.01 - EP); **C23C 16/18** (2013.01 - EP); **C23C 18/38** (2013.01 - KR)

Citation (search report)

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- [PX] DATABASE CA [online] CHEMICAL ABSTRACTS SERVICE, COLUMBUS, OHIO, US; RHEWE, SHI-WOO ET AL: "Property of hfac (hexafluoroacetylacetonate)Cu(I)DMB (3,3-dimethyl-1-butene) as a liquid precursor for chemical vapor deposition of copper films", XP002473287, retrieved from STN Database accession no. 132:159098 & HAN'GUK CHAELYO HAKHOECHI, 9(11), 1148-1152 CODEN: HCHAEU; ISSN: 1225-0562, 1999
- See references of WO 0063461A1

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